SN65C116xE 具有 ±15kV ESD 保护的双路差分驱动器和接收器

1 特性

- 达到或超出 TIA/EIA-422-B 和 ITU Recommendation V.11 标准的要求
- 使用 5V 单电源供电
- 为 RS-422 总线引脚提供 ESD 保护
  - ±15kV 人体放电模型 (HBM)
  - ±8kV IEC 61000-4-2，接触放电
  - ±8kV IEC 61000-4-2，空气间隙放电
- 低电源电流要求：9mA（最大值）
- 低脉冲偏斜
- 接收器输入阻抗：17kΩ（典型值）
- 接收器输入灵敏度：±200mV
- 接收器共模输入电压范围为 -7V 至 +7V
- 无干扰上电和断电保护
- 接收器三态输出低电平有效使能（仅限 SN65C1167E）

2 应用

- 交流和伺服电机驱动器
- 工厂自动化和控制
- 无线基础设施

3 说明

SN65C1167E 和 SN65C1168E 由双驱动器和双接收器组成，具有 ±15kV ESD（人体放电模型 [HBM]）和 ±8kV ESD（IEC61000-4-2 空气间隙放电和接触放电）保护，适用于 RS-422 总线引脚。这些器件符合 TIA/EIA-422-B 和 ITU 建议 V.11 的要求。

SN65C1167E 整合了双三态差分线路驱动器和三态差分线路接收器，两者均采用 5V 单电源供电。驱动器和接收器分别具有高电平有效和低电平有效使能端，它们可以在外部连接在一起，用作方向控制。

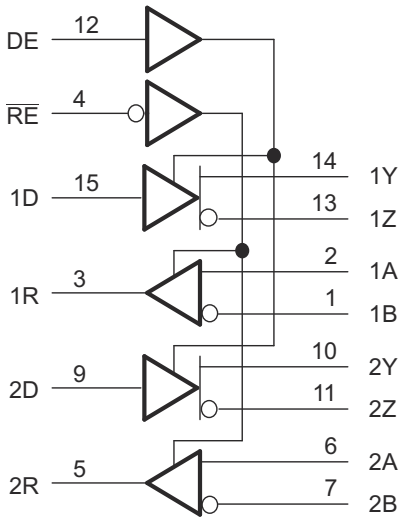
SN65C1168E 驱动器具有单独的高电平有效使能端。

封装信息

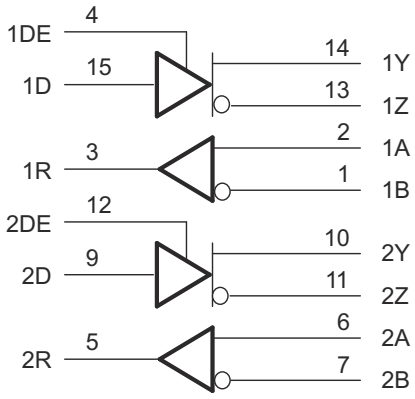
器件型号	封装(1)	封装尺寸(2)
SN65C116xE	SO (16)	10.3mm × 5.3mm
	TSSOP (16)	5mm × 4.4mm
	VQFN (16)	4mm x 3.5mm

(1) 有关更多信息，请参阅 节 11。
(2) 封装尺寸（长 × 宽）为标称值，并包括引脚（如适用）。

SN65C1167E



SN65C1168E



方框图

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4 Pin Configuration and Functions

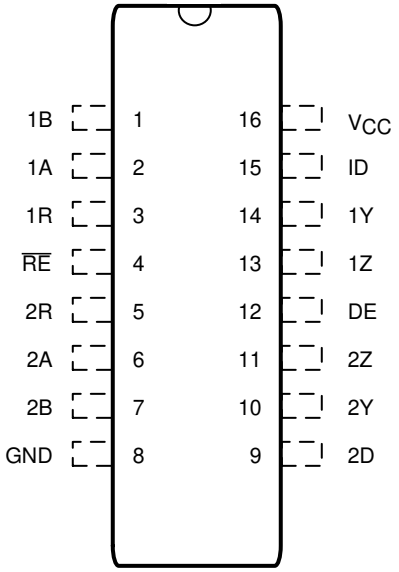


图 4-1. NS or PW Package 16 Pin (NS or TSSOP) Top View

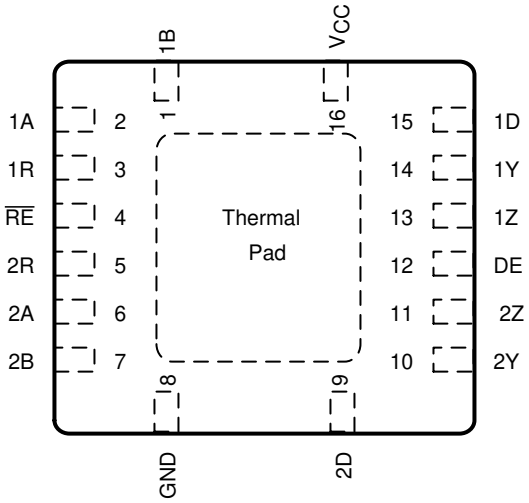


图 4-2. RGY Package 16 Pin (VQFN) Top View

表 4-1. Pin Functions, SN65C1167E

PIN				I/O	DESCRIPTION
NAME	SO	TSSOP	VQFN		
1A	2	2	2	I	RS422 differential input (noninverting) to receiver 1
2A	6	6	6	I	RS422 differential input (noninverting) to receiver 2
1B	1	1	1	I	RS422 differential input (inverting) to receiver 1
2B	7	7	7	I	RS422 differential input (inverting) to receiver 2
1D	15	15	15	I	Logic data input to RS422 driver 1
2D	9	9	9	I	Logic data input to RS422 driver 2
DE	12	12	12	I	Driver enable (active high)
GND	8	8	8	—	Device ground pin
1R	3	3	3	O	Logic data output of RS422 receiver 1
2R	5	5	5	O	Logic data output of RS422 receiver 2
$\overline{RE}$	4	4	4	I	Receiver enable pin (active low)
V_{CC}	16	16	16	—	Power supply
1Y	14	14	14	O	RS-422 differential (noninverting) driver output 1
2Y	10	10	10	O	RS-422 differential (noninverting) driver output 2
1Z	13	13	13	O	RS-422 differential (inverting) driver output 1
2Z	11	11	11	O	RS-422 differential (inverting) driver output 2

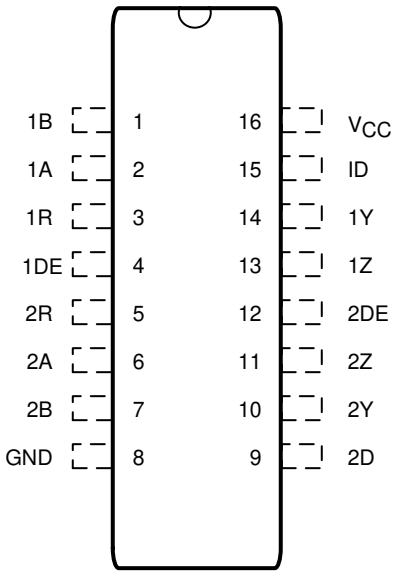


图 4-3. NS or PW Package 16 Pin (NS or TSSOP) Top View

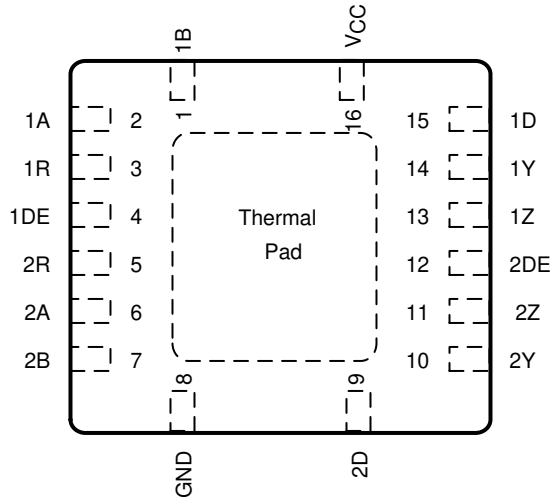


图 4-4. RGY Package 16 Pin (VQFN) Top View

表 4-2. Pin Functions, SN65C1168E

PIN				I/O	DESCRIPTION
NAME	SO	TSSOP	VQFN		
1A	2	2	2	I	RS422 differential input (noninverting) to receiver 1
2A	6	6	6	I	RS422 differential input (noninverting) to receiver 2
1B	1	1	1	I	RS422 differential input (inverting) to receiver 1
2B	7	7	7	I	RS422 differential input (inverting) to receiver 2
1D	15	15	15	I	Logic data input to RS422 driver 1
2D	9	9	9	I	Logic data input to RS422 driver 2
1DE	4	4	4	I	Driver 1 enable (active high)
2DE	12	12	12	I	Driver 2 enable (active high)
GND	8	8	8	—	Device ground
1R	3	3	3	O	Logic data output of RS422 receiver 1
2R	5	5	5	O	Logic data output of RS422 receiver 2
V_{CC}	16	16	16	—	Power supply
1Y	14	14	14	O	RS-422 differential (noninverting) driver output 1
2Y	10	10	10	O	RS-422 differential (noninverting) driver output 2
1Z	13	13	13	O	RS-422 differential (noninverting) driver output 1
2Z	11	11	11	O	RS-422 differential (noninverting) driver output 2

5 Specifications

5.1 Absolute Maximum Ratings

over recommended operating free-air temperature range (unless otherwise noted) (1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage(2)		– 0.5	7	V
V_I	Input voltage	Driver, DE, RE	– 0.5	7	V
		A or B, Receiver	– 14	14	
V_{ID}	Differential input voltage(3)	Receiver	– 14	14	V
V_O	Output voltage	Driver	– 0.5	7	V
		Receiver	– 0.5	V_{CC} + 0.5	
I_{IK}	Input clamp current	Driver, V_I < 0		– 20	mA
I_{OK}	Output clamp current	Driver, V_O < 0		– 20	mA
		Receiver		±20	
I_O	Output current	Driver		±150	mA
		Receiver		±25	
I_{CC}	Supply current			200	mA
	GND current			– 200	mA
T_J	Operating virtual junction temperature			150	°C
T_A	Operating free-air temperature		– 40	85	°C
T_{stg}	Storage temperature		– 65	150	°C

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltage values except differential input voltage are with respect to the network GND.
(3) Differential input voltage is measured at the noninverting terminal, with respect to the inverting terminal.

5.2 Driver Output and Receiver Input ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±15000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101(2)	±1000	
		IEC 61000-4-2, air-gap discharge	±8000	
		IEC 61000-4-2, contact discharge	±8000	

(1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

			MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage		4.5	5	5.5	V
V_{IC}	Common-mode input voltage(1)	Receiver			±7	V
V_{ID}	Differential input voltage	Receiver			±7	V
V_I	Input voltage	Except A, B	0		5.5	V
V_O	Output voltage	Receiver	0		V_{CC}	V
V_{IH}	High-level input voltage	Except A, B	2			V
V_{IL}	Low-level input voltage	Except A, B			0.8	V
I_{OH}	High-level output current	Receiver			–6	mA
		Driver			–20	
I_{OL}	Low-level output current	Receiver			6	mA
		Driver			20	
T_A	Operating free-air temperature		–40		85	°C

(1) Refer to TIA/EIA-422-B for exact conditions.

5.4 Thermal Information

THERMAL METRIC(1)		SN65C116xE			UNIT
		SO (NS)	PW (TSSOP)	RGY (VQFN)	
		16 PINS	16 PINS	16 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	88.5	107.5	48.4	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	46.2	38.4	46.4	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	50.7	53.7	24.6	°C/W
ψ_{JT}	Junction-to-top characterization parameter	13.5	3.2	2.3	°C/W
ψ_{JB}	Junction-to-board characterization parameter	50.3	53.1	24.5	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	n/a	n/a	8.5	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, SPRA953.

5.5 Driver Section Electrical Characteristics

over recommended supply voltage and operating free-air temperature ranges (unless otherwise noted)

PARAMETER		TEST CONDITIONS			MIN	TYP(1)	MAX	UNIT
V_{IK}	Input clamp voltage	I_I = –18mA					–1.5	V
V_{OH}	High-level output voltage	V_{IH} = 2V,	V_{IL} = 0.8V,	I_{OH} = –20mA	2.4	3.5		V
V_{OL}	Low-level output voltage	V_{IH} = 2V,	V_{IL} = 0.8V,	I_{OL} = 20mA		0.2	0.4	V
$\|V_{OD1}\|$	Differential output voltage 1	I_O = 0mA			2		6	V
$\|V_{OD2}\|$	Differential output voltage 2	R_L = 100Ω,	See 图 6-1 (2)		2	3.7		V
$\Delta\|V_{OD}\|$	Change in magnitude of differential output voltage	R_L = 100Ω,	See 图 6-1 (2)				±0.4	V
V_{OC}	Common-mode output voltage	R_L = 100Ω,	See 图 6-1 (2)				±3	V
$\Delta\|V_{OC}\|$	Change in magnitude of common-mode output voltage	R_L = 100Ω,	See 图 6-1 (2)				±0.4	V
$I_{O(OFF)}$	Output current with power off	V_{CC} = 0V	V_O = 6V				100	µA
			V_O = –0.25V				100	
I_{OZ}	High-impedance-state output current	V_O = 2.5V					20	µA
		V_O = 5V					–20	
I_{IH}	High-level input current	V_I = V_{CC} or V_{IH}					1	µA
I_{IL}	Low-level input current	V_I = GND or V_{IL}					–1	µA
I_{OS}	Short-circuit output current	V_O = V_{CC} or GND(3)			–30		–150	mA
I_{CC}	Supply current (total package)	No load, Enabled	V_I = V_{CC} or GND			4	6	mA
			V_I = 2.4 or 0.5V(4)			5	9	
C_i	Input capacitance					6		pF

(1) All typical values are at V_{CC} = 5V and T_A = 25°C.
(2) Refer to TIA/EIA-422-B for exact conditions.
(3) Not more than one output should be shorted at a time, and the duration of the short circuit should not exceed one second.
(4) This parameter is measured per input, while the other inputs are at V_{CC} or GND.

5.6 Receiver Section Electrical Characteristics

over recommended ranges of common-mode input voltage, supply voltage, and operating free-air temperature (unless otherwise noted)

PARAMETER			TEST CONDITIONS		MIN	TYP(1)	MAX	UNIT
V_{IT+}	Positive-going input threshold voltage, differential input						0.2	V
V_{IT-}	Negative-going input threshold voltage, differential input				–0.2(2)			V
V_{hys}	Input hysteresis (V_{IT+} – V_{IT-})					60		mV
V_{IK}	Input clamp voltage, $\overline{RE}$	SN65C1167E	I_I = –18mA				–1.5	V
V_{OH}	High-level output voltage		V_{ID} = 200mV,	I_{OH} = –6mA	3.8	4.2		V
V_{OL}	Low-level output voltage		V_{ID} = –200mV,	I_{OL} = 6mA		0.1	0.3	V
I_{OZ}	High-impedance state output current	SN65C1167E	V_O = V_{CC} or GND			±0.5	±5	µA
I_I	Line input current		Other input at 0V	V_I = 10V			1.5	mA
				V_I = –10V			–2.5	
I_I	Enable input current, $\overline{RE}$	SN65C1167E	V_I = V_{CC} or GND				±1	µA
r_I	Input resistance		V_{IC} = –7V to 7V,	Other input at 0V	4	17		kΩ
I_{CC}	Supply current (total package)		No load, Enabled	V_I = V_{CC} or GND		4	6	mA
				V_{IH} = 2.4V or 0.5V(3)		5	9	

(1) All typical values are at V_{CC} = 5V and T_A = 25°C.
(2) The algebraic convention, where the less positive (more negative) limit is designated as minimum, is used in this data sheet for common-mode input voltage and threshold voltage levels only.
(3) Refer to TIA/EIA-422-B for exact conditions.

5.7 Driver Section Switching Characteristics

over recommended supply voltage and operating free-air temperature ranges (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP(1)	MAX	UNIT
t_{PHL}	Propagation delay time, high- to low-level output	R1 = R2 = 50Ω, C1 = C2 = C3 = 40pF, See 图 6-2	R3 = 500Ω, S1 is open,		8	16	ns
t_{PLH}	Propagation delay time, low- to high-level output				8	16	ns
$t_{sk(p)}$	Pulse skew				1.5	4	ns
t_r	Rise time	R1 = R2 = 50Ω, C1 = C2 = C3 = 40pF, See 图 6-3	R3 = 500Ω, S1 is open,		5	8	ns
t_f	Fall time				5	8	ns
t_{PZH}	Output-enable time to high level	R1 = R2 = 50Ω, C1 = C2 = C3 = 40pF, See 图 6-4	R3 = 500Ω, S1 is closed,		10	19	ns
t_{PZL}	Output-enable time to low level				10	19	ns
t_{PHZ}	Output-disable time from high level	R1 = R2 = 50Ω, C1 = C2 = C3 = 40pF, See 图 6-4	R3 = 500Ω, S1 is closed,		7	16	ns
t_{PLZ}	Output-disable time from low level				7	16	ns
f_{SW}	Maximum switching frequency	R1 = R2 = 50Ω, C1 = C2 = C3 = 40pF, See 图 6-3	R3 = 500Ω, S1 is open,	20			MHz

(1) All typical values are at V_{CC} = 5V and T_A = 25°C.

5.8 Receiver Section Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted)(2)

PARAMETER			TEST CONDITIONS		MIN	TYP(1)	MAX	UNIT
t_{PLH}	Propagation delay time, low- to high-level output		See 图 6-5		9	15	27	ns
t_{PHL}	Propagation delay time, high- to low-level output		See 图 6-5		9	15	27	ns
t_{TLH}	Transition time, low- to high-level output		V_{IC} = V,	See 图 6-5		4	9	ns
t_{THL}	Transition time, high- to low-level output					4	9	ns
t_{PZH}	Output-enable time to high level	SN65C1167E	R_L = 1kΩ, C_L= 50pF	See 图 6-6		7	22	ns
t_{PZL}	Output-enable time to low level					7	22	ns
t_{PHZ}	Output-disable time from high level					12	22	ns
t_{PLZ}	Output-disable time from low level					12	22	ns

(1) All typical values are at V_{CC} = 5V and T_A = 25°C.
(2) Measured per input while the other inputs are at V_{CC} or GND

6 Parameter Measurement Information

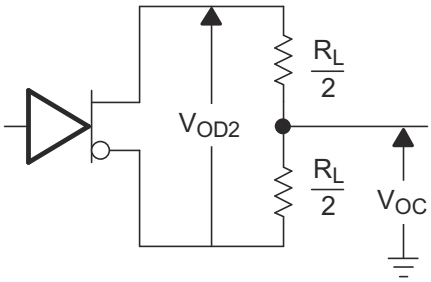
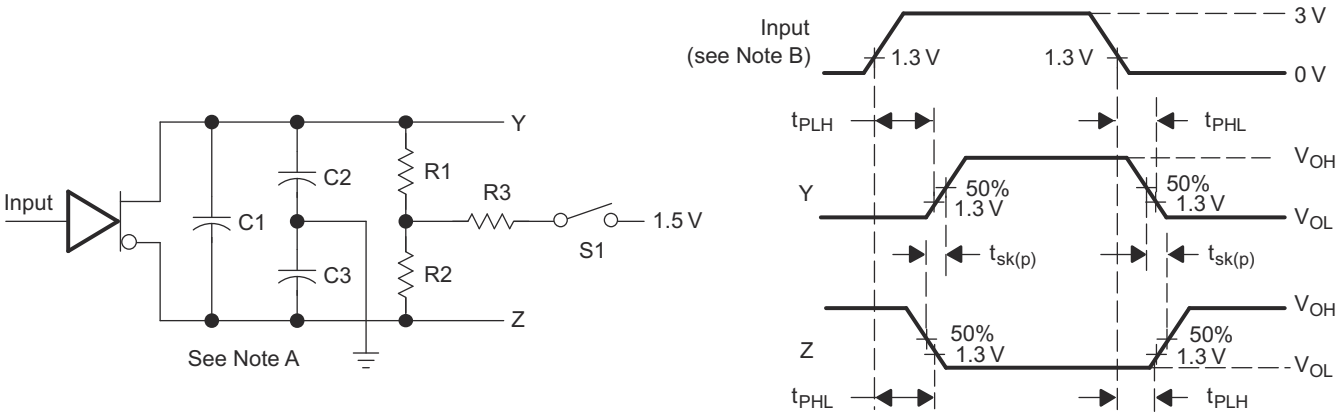


图 6-1. Driver Test Circuit, V_{OD} and V_{OC}

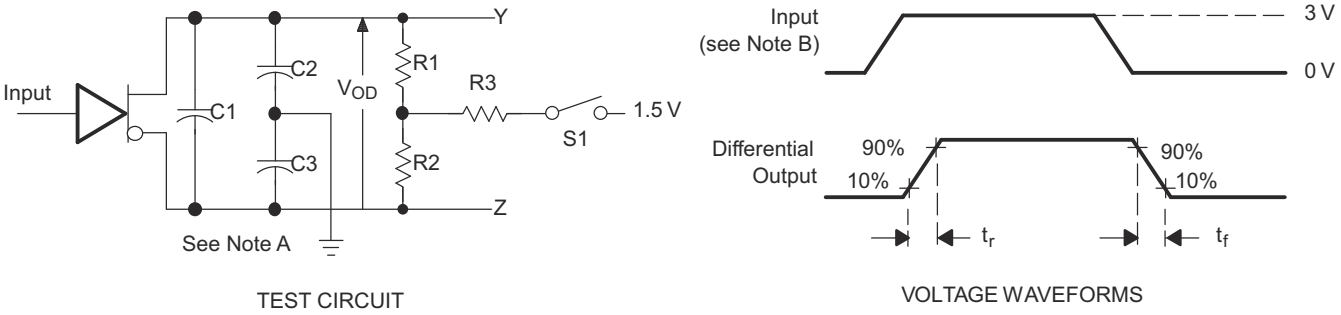


TEST CIRCUIT　　VOLTAGE WAVEFORMS

A. C1, C2, and C3 include probe and jig capacitance.

B. The input pulse is supplied by a generator having the following characteristics: PRR = 1 MHz, duty cycle = 50%, $t_r = t_f \leq 6$ns.

图 6-2. Driver Test Circuit and Voltage Waveforms

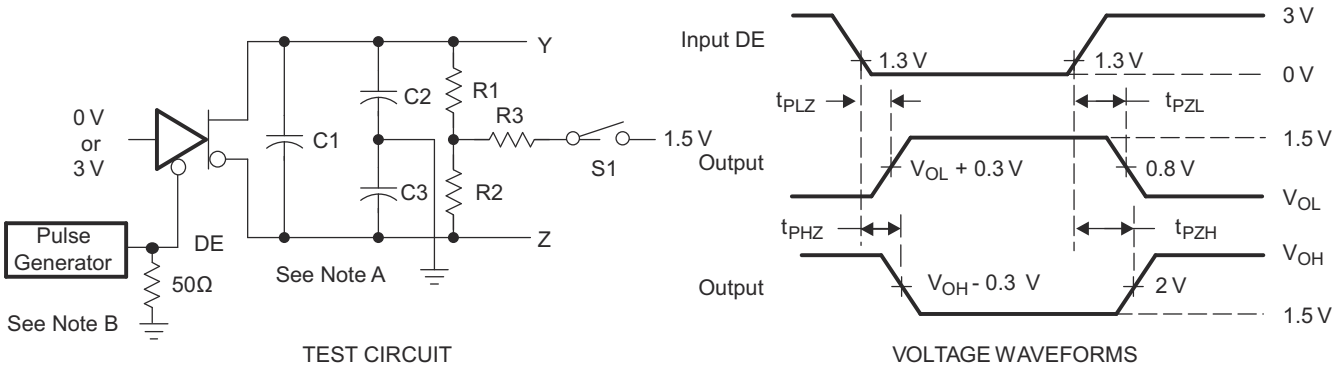


TEST CIRCUIT　　VOLTAGE WAVEFORMS

A. C1, C2, and C3 include probe and jig capacitance.

B. The input pulse is supplied by a generator having the following characteristics: PRR = 1 MHz, duty cycle = 50%, $t_r = t_f \leq 6$ns.

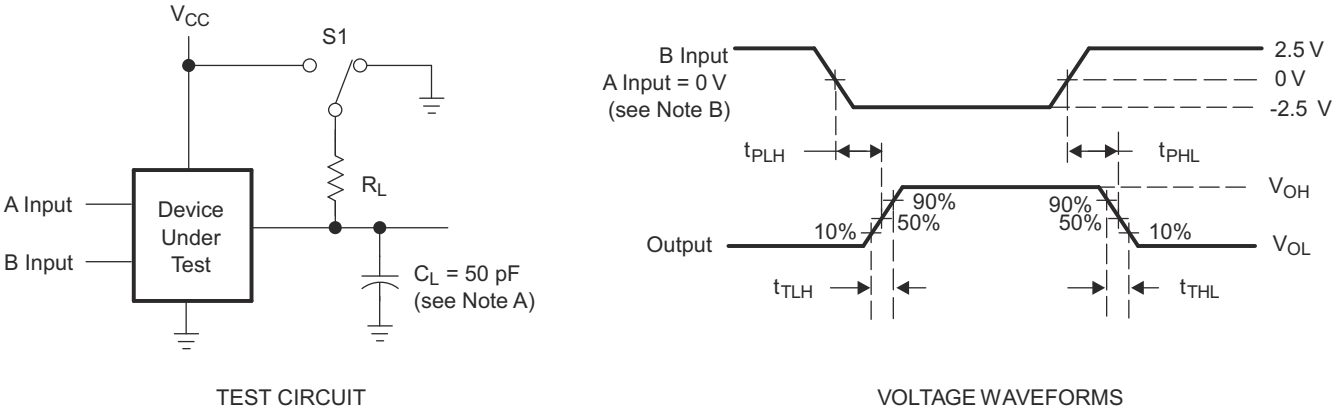
图 6-3. Driver Test Circuit and Voltage Waveforms



A. C1, C2, and C3 include probe and jig capacitance.

B. The input pulse is supplied by a generator having the following characteristics: PRR = 1 MHz, duty cycle = 50%, $t_r = t_f \leqslant 6$ns.

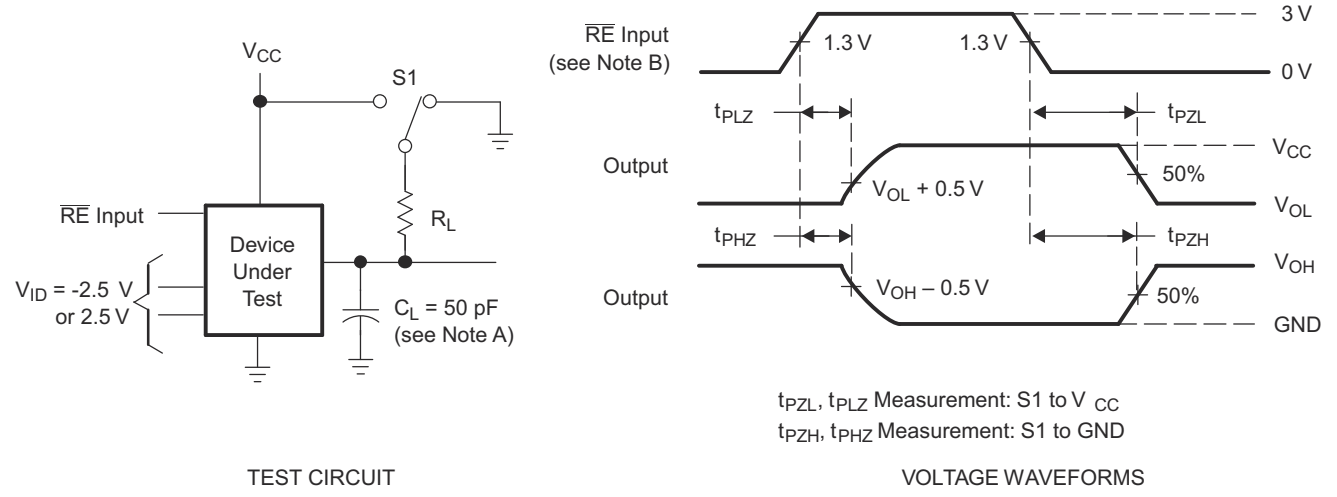
图 6-4. Driver Test Circuit and Voltage Waveforms



A. C1, C2, and C3 include probe and jig capacitance.

B. The input pulse is supplied by a generator having the following characteristics: PRR = 1 MHz, duty cycle = 50%, $t_r = t_f \leqslant 6$ns.

图 6-5. Receiver Test Circuit and Voltage Waveforms



A. C1, C2, and C3 include probe and jig capacitance.

B. The input pulse is supplied by a generator having the following characteristics: PRR = 1 MHz, duty cycle = 50%, $t_r = t_f \leqslant 6$ns.

图 6-6. Receiver Test Circuit and Voltage Waveforms

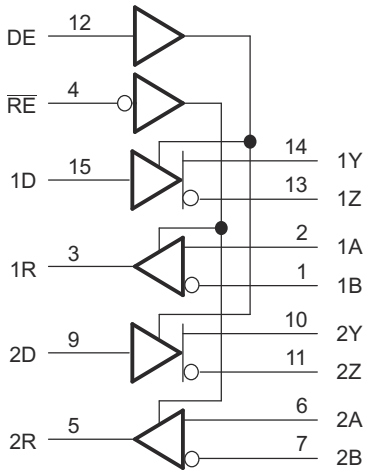
7 Detailed Description

7.1 Overview

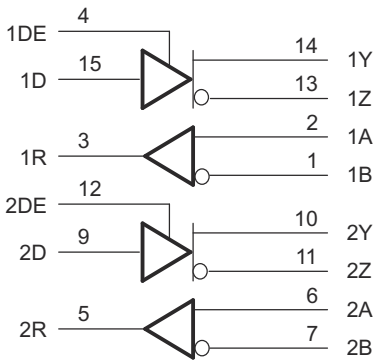
The SN65C1167E and SN65C1168E consist of dual drivers and dual receivers powered from a single 5V supply. These devices meet the requirements of TIA/EIA-422-B and ITU recommendation V.11.

7.2 Functional Block Diagram

SN65C1167E



SN65C1168E



7.3 Feature Description

7.3.1 Active High Driver Output Enables

Both drivers of SN65C1167E can be configured with the single DE logic input. Both drivers are set at high-impedance when disabled.

SN65C1168E drivers can be configured individually by 1DE and 2DE logic inputs. Both drivers are set at high-impedance when disabled.

7.3.2 Active Low Receiver Enables

Both SN65C1167E receivers can be configured with the single $\overline{RE}$ logic input. Receiver logic outputs are set at high-impedance when disabled.

7.4 Device Functional Modes

表 7-1 and 表 7-2 list the functional modes of SN65C1167E and SN65C1168E.

表 7-1. Each Driver

INPUT D	ENABLE DE	OUTPUTS	
		Y	Z
H	H	H	L
L	H	L	H
X	L	Z	Z

表 7-2. SN65C1167E, Each Receiver(1)

DIFFERENTIAL INPUTS A – B	ENABLE $\overline{RE}$	OUTPUT R
$V_{ID} \geq 0.2$ V	L	H
-0.2 V < V_{ID} < 0.2 V	L	?
$V_{ID} \leq -0.2$ V	L	L
X	H	Z
Open	L	H

(1) H = High level, L = Low level, ? = Indeterminate, X = Irrelevant, Z = High impedance (off)

表 7-3. SN65C1168E, Each Receiver(1)

DIFFERENTIAL INPUTS A – B	OUTPUT R
$V_{ID} \geq 0.2$V	H
-0.2V < V_{ID} < 0.2V	?
$V_{ID} \leq -0.2$V	L
Open	H

(1) H = High level, L = Low level, ? = Indeterminate

8 Application and Implementation

备注

以下应用部分中的信息不属于 TI 器件规格的范围，TI 不担保其准确性和完整性。TI 的客 户应负责确定器件是否适用于其应用。客户应验证并测试其设计，以确保系统功能。

8.1 Application Information

图 8-1 shows a typical RS-422 application. One transmitter is able to broadcast to multiple receiving nodes connected together over a shared differential bus. Twisted-pair cabling with a controlled differential impedance is used, and a termination resistance is placed at the farthest receive end of the cable in order to match the transmission line impedance and minimize signal reflections.

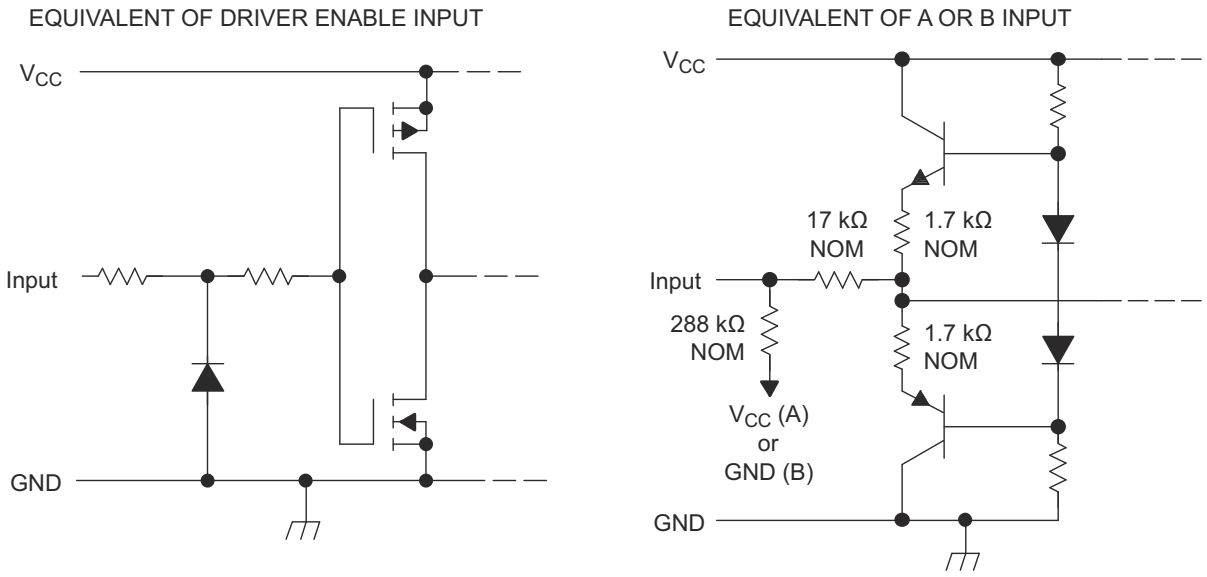


图 8-1. Schematic of Inputs

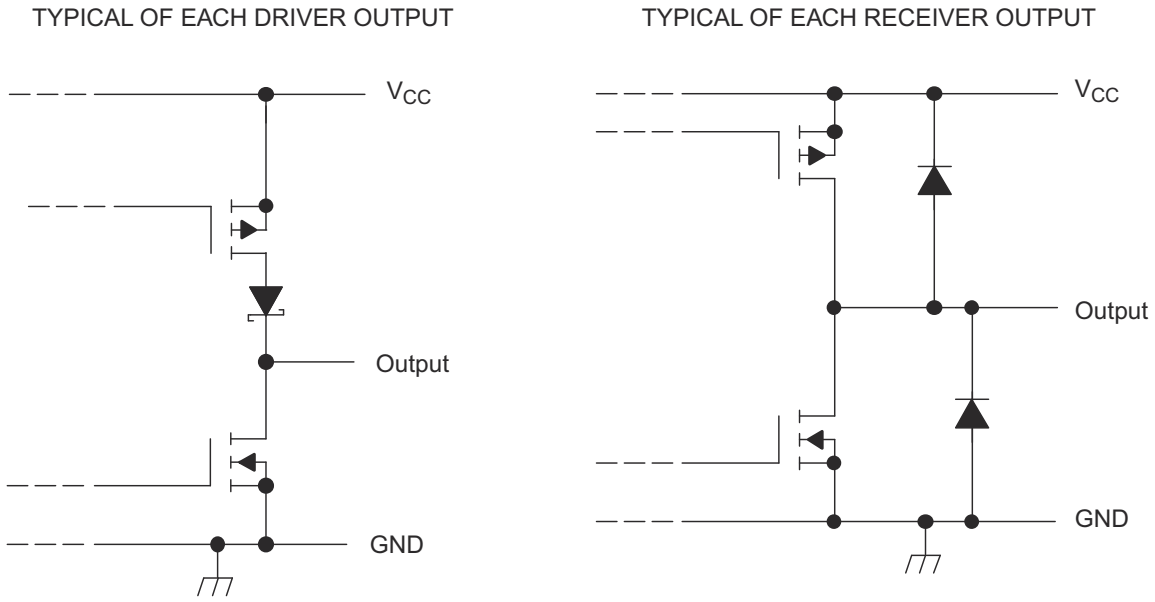


图 8-2. Schematic of Outputs

8.2 Typical Application

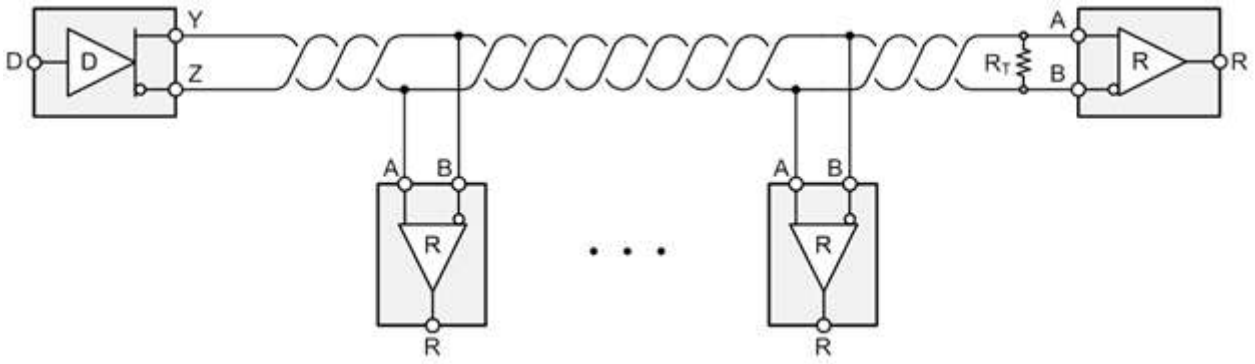


图 8-3. Typical RS-422 Application

8.2.1 Design Requirements

A typical RS-422 implementation using SN65C116xE requires the following:

- 5V power source.
- Connector that ensures the correct polarity for port pins.
- Cabling that supports the desired operating rate and transmission distance.

8.2.2 Detailed Design Procedure

Place the device close to bus connector to keep traces (stub) short to prevent adding reflections to the bus line. If desired, add external fail-safe biasing to ensure ±200 mV on the A-B port when the driver circuit is disabled.

8.3 Power Supply Recommendations

Use a 5V power supply for V_{CC} place 0.1 μF bypass capacitors close to the power supply pins to reduce errors coupling in from noisy or high impedance power supplies.

9 Device and Documentation Support

9.1 Device Support

9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on Alert me to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

9.3 支持资源

TI E2E™ 中文支持论坛是工程师的重要参考资料，可直接从专家处获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题，获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的使用条款。

9.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.
所有商标均为其各自所有者的财产。

9.5 静电放电警告

静电放电 (ESD) 会损坏这个集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

9.6 术语表

TI 术语表	本术语表列出并解释了术语、首字母缩略词和定义。

10 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision B (May 2017) to Revision C (February 2024)	Page
• 将“器件信息”表更改为“封装信息”表	1
• Deleted the thermal packaging information from the *Absolute Maximum Ratings*	5
• Changed the *Thermal Information* table	6

Changes from Revision A (April 2007) to Revision B (May 2017)	Page
• 添加了 *ESD 等级* 表、*特性说明* 部分、*器件功能模式*、*应用和实施* 部分、*电源相关建议* 部分、*器件和文档支持* 部分以及 *机械、封装和可订购信息* 部分	1
• Changed the Rise Time Max value From: 10 ns To: 8 ns in the *Driver Section Switching Characteristics* table	8
• Changed the Fall Time Max value From: 10 ns To: 8 ns in the *Driver Section Switching Characteristics* table.	8
• Added Maximum switching frequency to the *Driver Section Switching Characteristics* table	8

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
SN65C1167ENS	Obsolete	Production	SOP (NS) | 16	-	-	Call TI	Call TI	-40 to 85	65C1167E
SN65C1167ENSR	Active	Production	SOP (NS) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C1167E
SN65C1167ENSR.A	Active	Production	SOP (NS) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C1167E
SN65C1167ENSRG4	Active	Production	SOP (NS) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C1167E
SN65C1167ENSRG4.A	Active	Production	SOP (NS) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C1167E
SN65C1167EPW	Obsolete	Production	TSSOP (PW) | 16	-	-	Call TI	Call TI	-40 to 85	CB1167E
SN65C1167EPWR	Active	Production	TSSOP (PW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB1167E
SN65C1167EPWR.A	Active	Production	TSSOP (PW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB1167E
SN65C1167EPWRG4	Active	Production	TSSOP (PW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB1167E
SN65C1167EPWRG4.A	Active	Production	TSSOP (PW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB1167E
SN65C1167ERGYR	Active	Production	VQFN (RGY) | 16	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB1167
SN65C1167ERGYR.A	Active	Production	VQFN (RGY) | 16	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB1167
SN65C1167ERGYRG4	Active	Production	VQFN (RGY) | 16	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB1167
SN65C1167ERGYRG4.A	Active	Production	VQFN (RGY) | 16	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB1167
SN65C1168ENS	Obsolete	Production	SOP (NS) | 16	-	-	Call TI	Call TI	-40 to 85	65C1168E
SN65C1168ENSR	Active	Production	SOP (NS) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C1168E
SN65C1168ENSR.A	Active	Production	SOP (NS) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C1168E
SN65C1168EPW	Obsolete	Production	TSSOP (PW) | 16	-	-	Call TI	Call TI	-40 to 85	CB1168E
SN65C1168EPWR	Active	Production	TSSOP (PW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB1168E
SN65C1168EPWR.A	Active	Production	TSSOP (PW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB1168E
SN65C1168EPWRG4	Active	Production	TSSOP (PW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB1168E
SN65C1168ERGYR	Active	Production	VQFN (RGY) | 16	3000 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CB1168
SN65C1168ERGYR.A	Active	Production	VQFN (RGY) | 16	3000 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CB1168
SN65C1168ERGYRG4	Active	Production	VQFN (RGY) | 16	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB1168
SN65C1168ERGYRG4.A	Active	Production	VQFN (RGY) | 16	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB1168

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

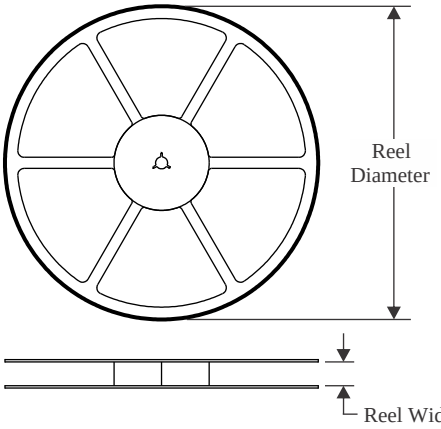
Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

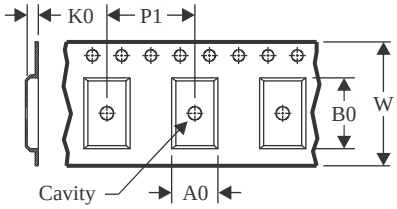
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

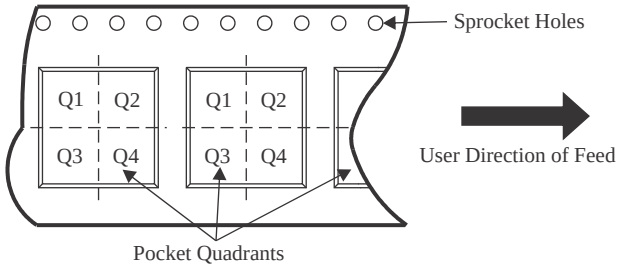


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

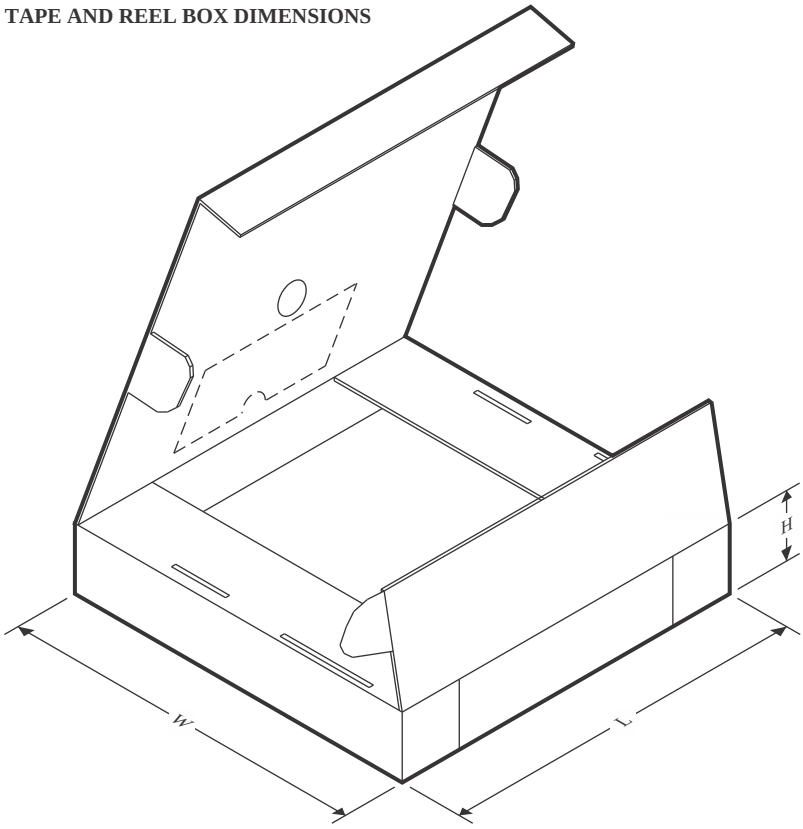
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

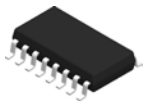
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65C1167ENSR	SOP	NS	16	2000	330.0	16.4	8.1	10.4	2.5	12.0	16.0	Q1
SN65C1167ENSRG4	SOP	NS	16	2000	330.0	16.4	8.1	10.4	2.5	12.0	16.0	Q1
SN65C1167EPWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN65C1167EPWRG4	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN65C1167ERGYR	VQFN	RGY	16	3000	330.0	12.4	3.8	4.3	1.5	8.0	12.0	Q1
SN65C1167ERGYRG4	VQFN	RGY	16	3000	330.0	12.4	3.8	4.3	1.5	8.0	12.0	Q1
SN65C1168ENSR	SOP	NS	16	2000	330.0	16.4	8.1	10.4	2.5	12.0	16.0	Q1
SN65C1168EPWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN65C1168ERGYR	VQFN	RGY	16	3000	330.0	12.4	3.8	4.3	1.5	8.0	12.0	Q1
SN65C1168ERGYRG4	VQFN	RGY	16	3000	330.0	12.4	3.8	4.3	1.5	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65C1167ENSR	SOP	NS	16	2000	353.0	353.0	32.0
SN65C1167ENSRG4	SOP	NS	16	2000	353.0	353.0	32.0
SN65C1167EPWR	TSSOP	PW	16	2000	353.0	353.0	32.0
SN65C1167EPWRG4	TSSOP	PW	16	2000	353.0	353.0	32.0
SN65C1167ERGYR	VQFN	RGY	16	3000	360.0	360.0	36.0
SN65C1167ERGYRG4	VQFN	RGY	16	3000	360.0	360.0	36.0
SN65C1168ENSR	SOP	NS	16	2000	353.0	353.0	32.0
SN65C1168EPWR	TSSOP	PW	16	2000	353.0	353.0	32.0
SN65C1168ERGYR	VQFN	RGY	16	3000	360.0	360.0	36.0
SN65C1168ERGYRG4	VQFN	RGY	16	3000	360.0	360.0	36.0

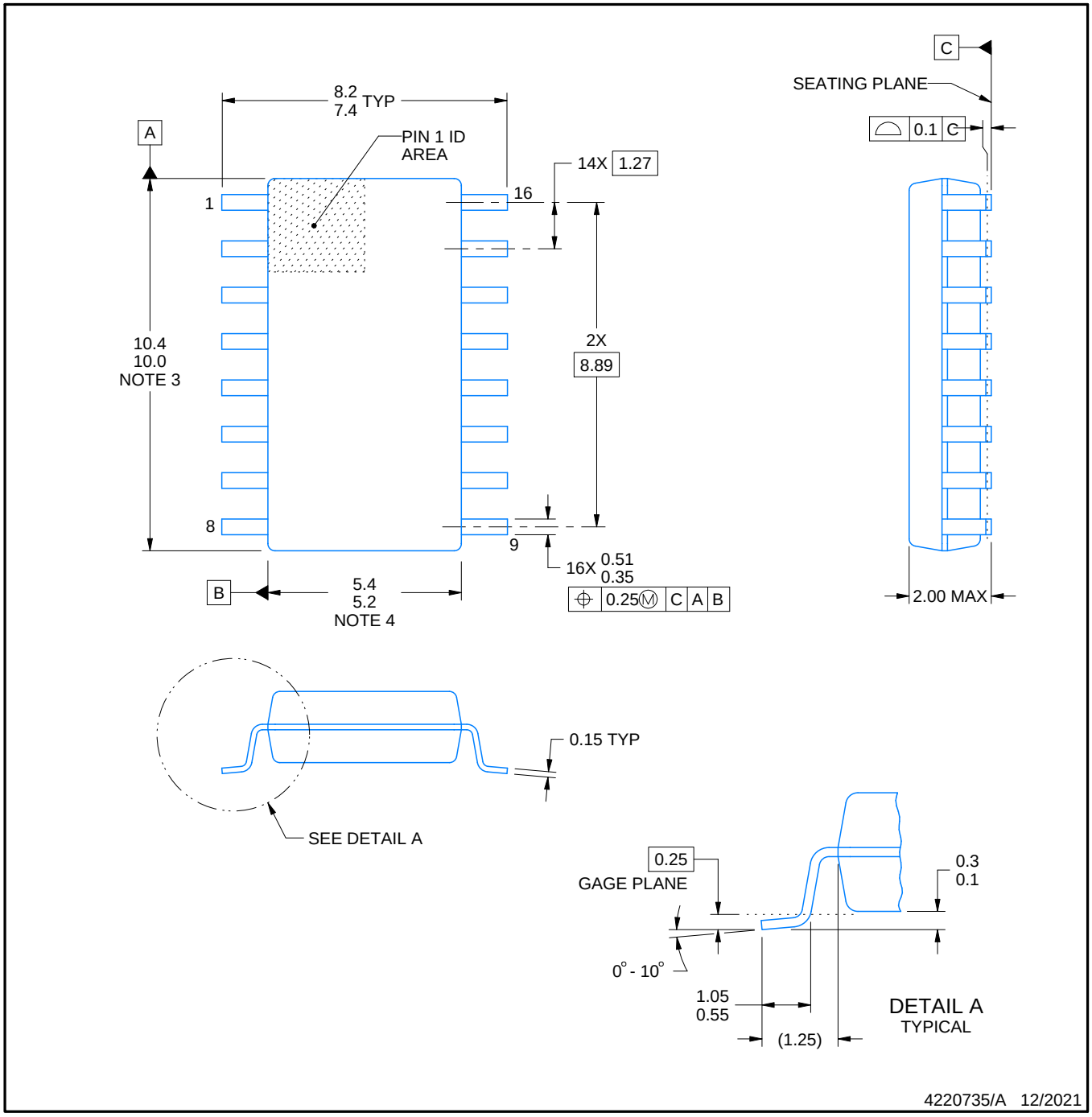


PACKAGE OUTLINE

NS0016A

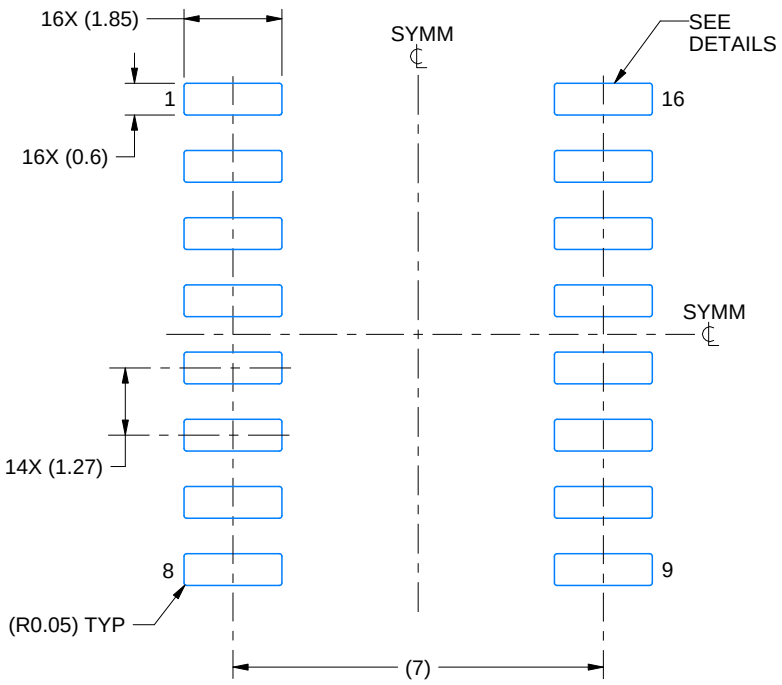
SOP - 2.00 mm max height

SOP

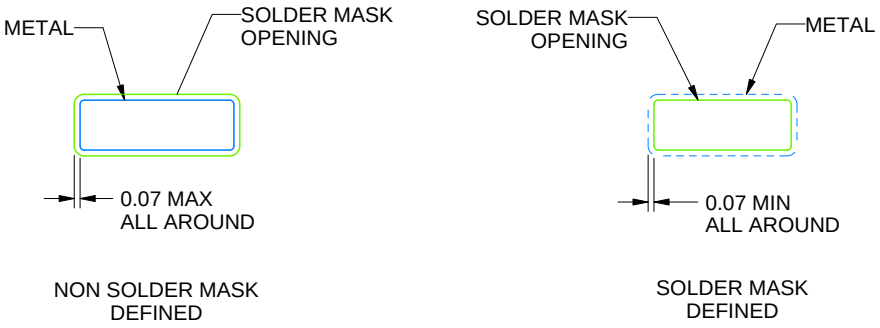


NOTES:

1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm, per side.



LAND PATTERN EXAMPLE
SCALE:7X



NON SOLDER MASK
DEFINED

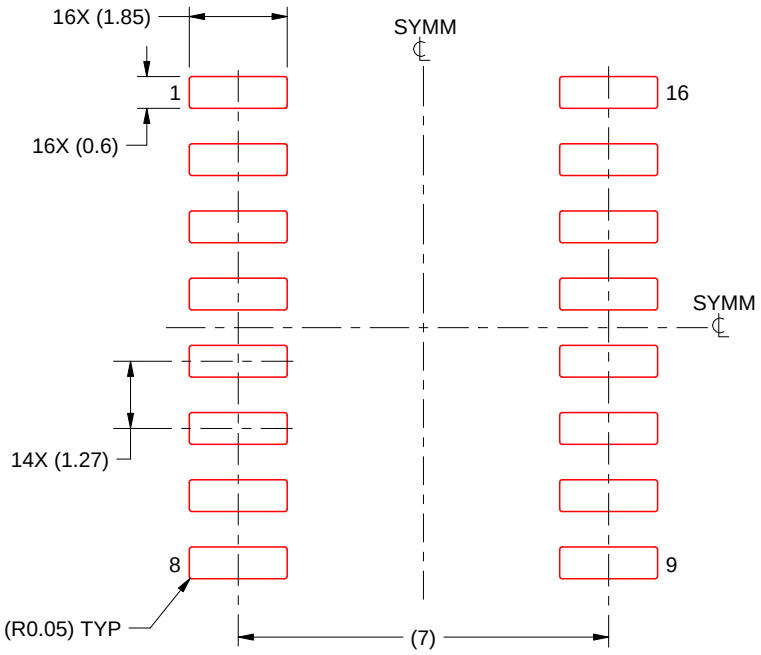
SOLDER MASK
DEFINED

SOLDER MASK DETAILS

4220735/A 12/2021

NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.
6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:7X

4220735/A 12/2021

NOTES: (continued)

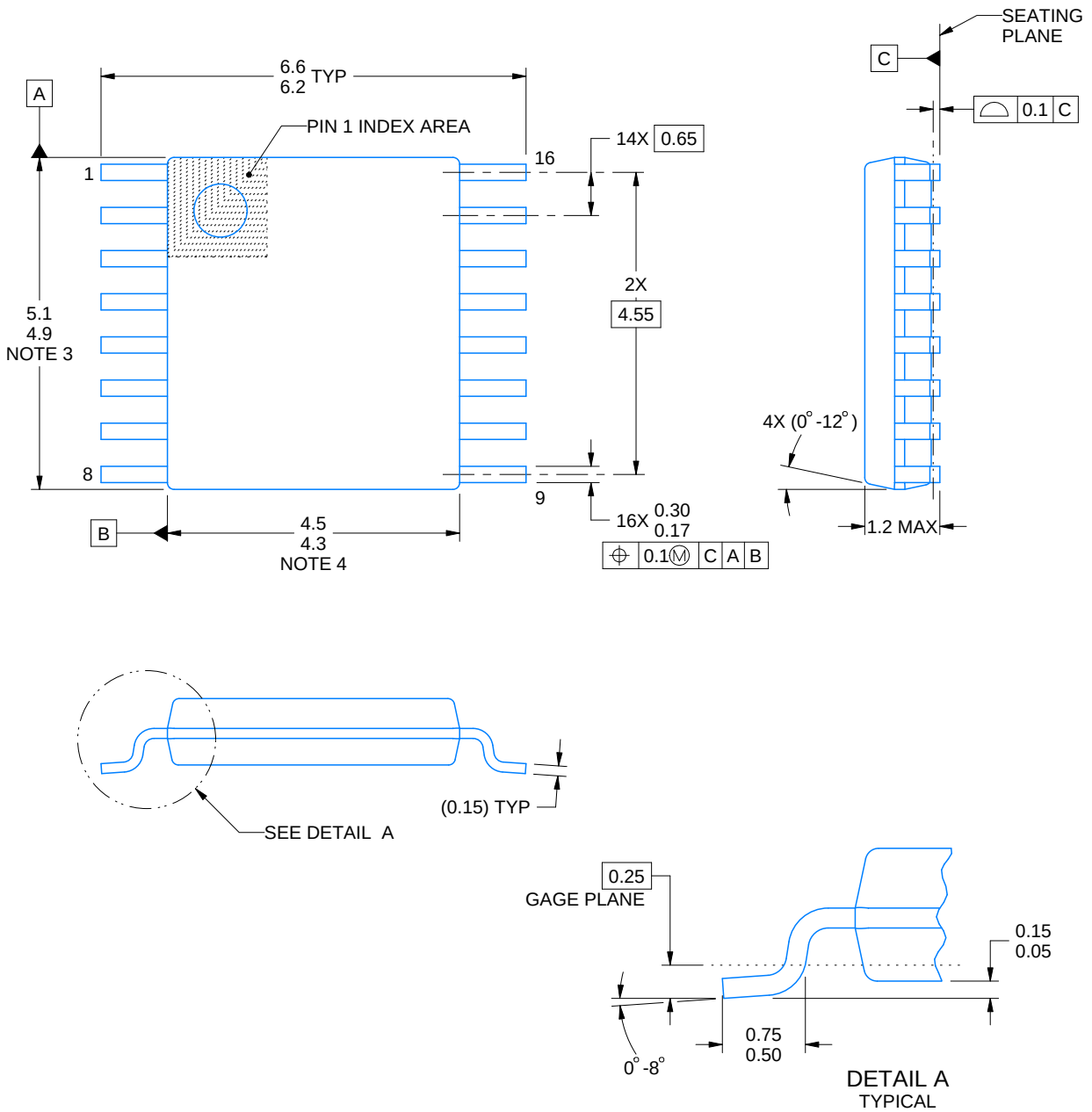
7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

PACKAGE OUTLINE

PW0016A

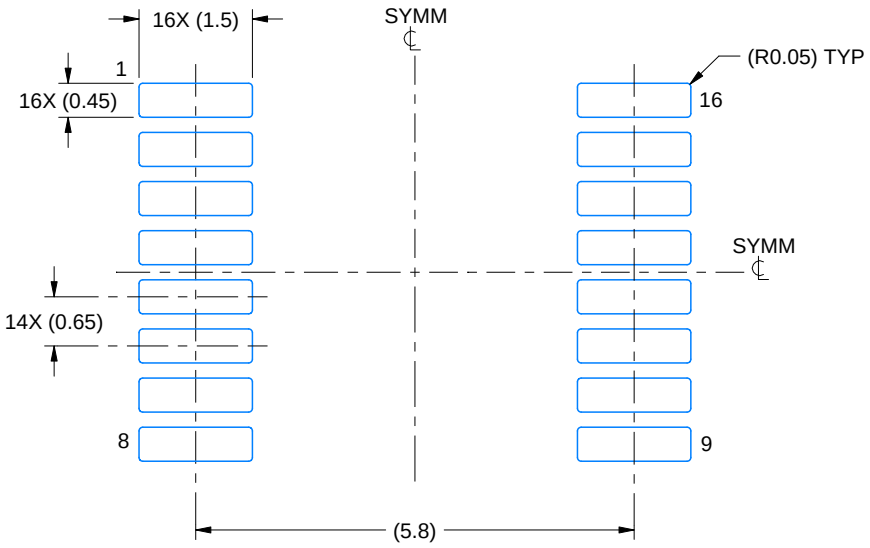
TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.



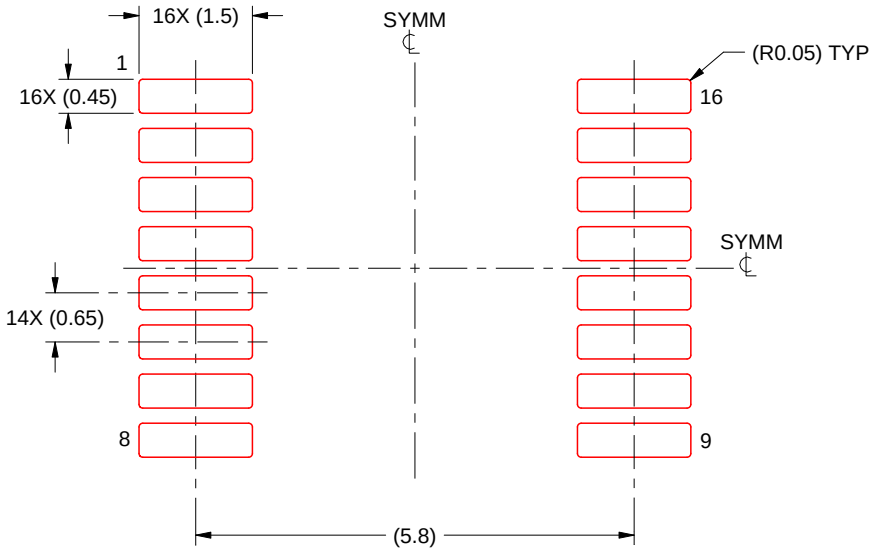
LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X

SOLDER MASK DETAILS

4220204/B 12/2023

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



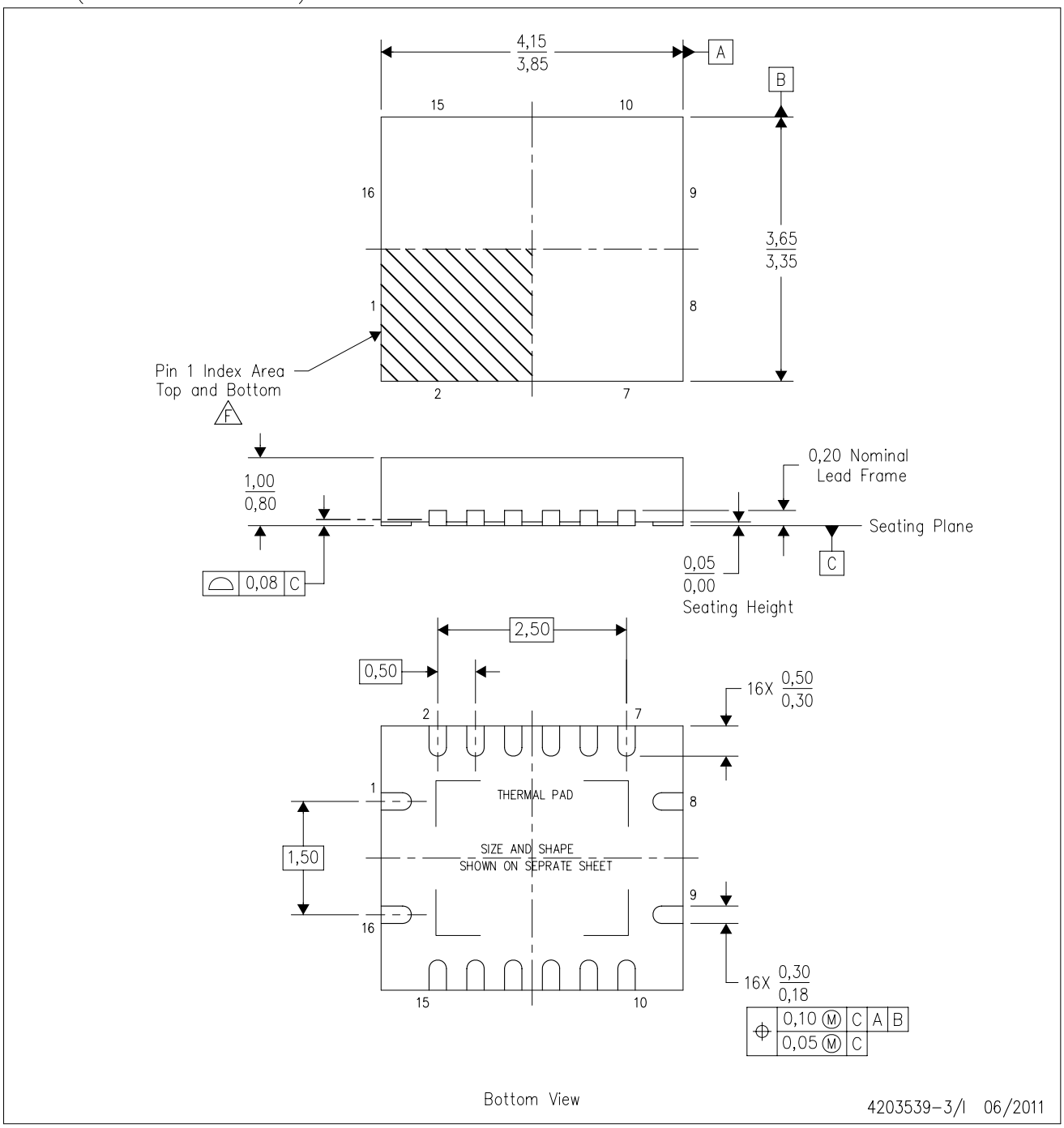
SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220204/B 12/2023

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

RGY (R–PVQFN–N16) PLASTIC QUAD FLATPACK NO–LEAD



NOTES:
A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. QFN (Quad Flatpack No–Lead) package configuration.
D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
F. Pin 1 identifiers are located on both top and bottom of the package and within the zone indicated. The Pin 1 identifiers are either a molded, marked, or metal feature.
G. Package complies to JEDEC MO–241 variation BA.

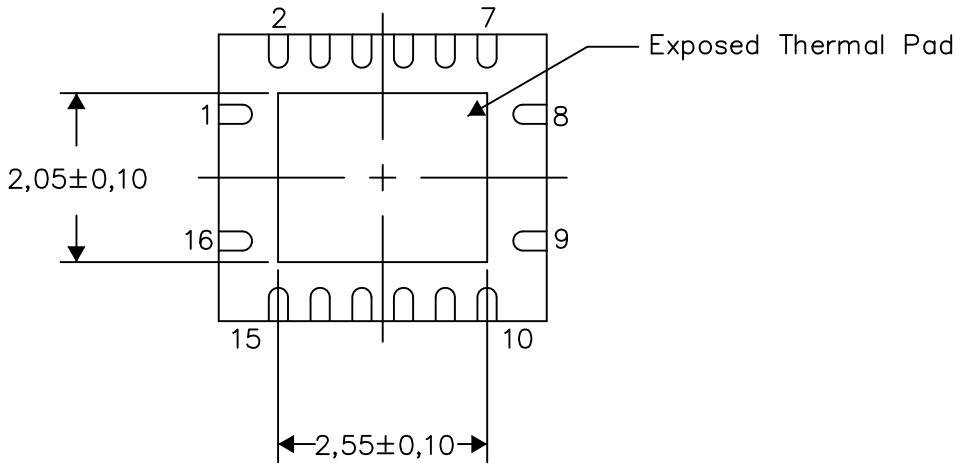
RGY (R–PVQFN–N16) PLASTIC QUAD FLATPACK NO–LEAD

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No–Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



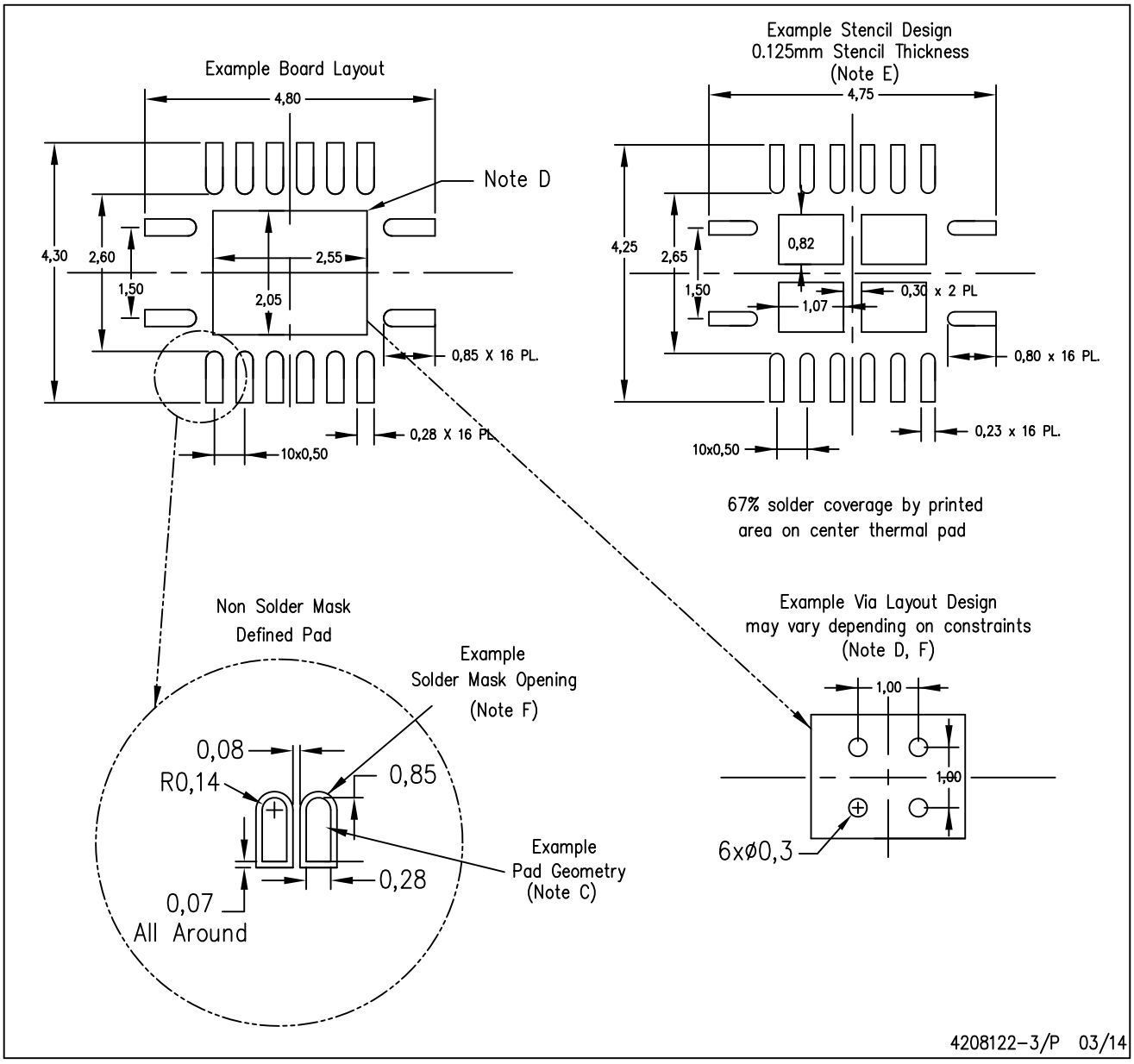
Bottom View

Exposed Thermal Pad Dimensions

4206353–3/P 03/14

NOTE: All linear dimensions are in millimeters

RGY (R–PVQFN–N16) PLASTIC QUAD FLATPACK NO–LEAD



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat–Pack QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <http: //www.ti.com>.
E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
F. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.

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